

## Description

The PSJMTOF65R650 is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

### MOSFET Product Summary

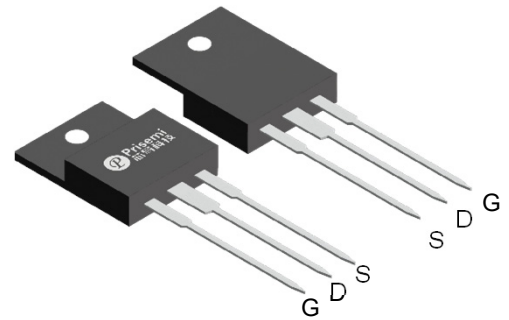
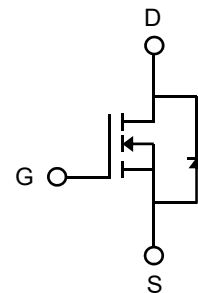
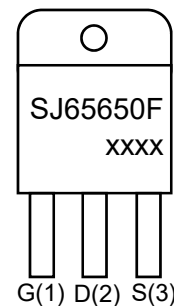
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)(Typ)$	$I_D(A)$
650	519@ $V_{GS} = 10V$	4.8

## Feature

- Fast Switching Capability
- Lead free product is acquired.
- Avalanche Energy Tested

## Applications

- PWM applications
- Load Switch
- Power Management
- DC-DC Converters


**TO-220F**

**Circuit Diagram**


G(1) D(2) S(3)

**Marking (Top View)**

## Absolute maximum rating@25°C

Rating		Symbol	Value	Units
Drain-Source Voltage		$V_{DS}$	650	V
Gate-Source Voltage		$V_{GS}$	±30	V
Drain Current-Continuous <sup>1)</sup>	$T_C=25^\circ C$	$I_D$	4.8	A
	$T_C=100^\circ C$		3.0	
Pulsed Drain Current <sup>2)</sup>		$I_{DM}$	10	A
Total Power Dissipation <sup>3)</sup>		$P_D$	80.6	W
Avalanche Current <sup>4)</sup>		$I_{AS}$	4.5	A
Avalanche Energy <sup>4)</sup>		$E_{AS}$	199.5	mJ
Thermal Resistance , Junction-to-Case <sup>5)</sup>		$R_{\theta JC}$	1.5	°C/W
Thermal Resistance , Junction-to-Ambient <sup>6)</sup>		$R_{\theta JA}$	47.5	°C/W
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~+150	°C

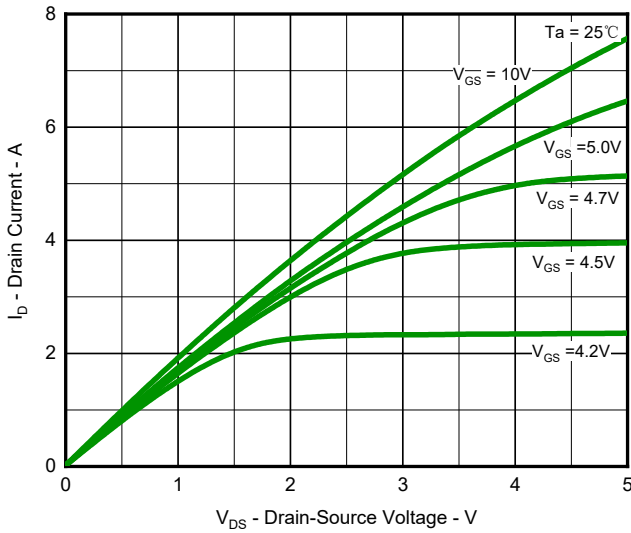
## Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 650V, V_{GS} = 0V$	-	-	1.0	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	2.9	3.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 1A$	-	519	650	m $\Omega$
<b>Dynamic Characteristics<sup>7)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 100V, V_{GS} = 0V,$ $f = 1.0MHz$	-	334.3	-	pF
Output Capacitance	$C_{oss}$		-	16.2	-	
Reverse Transfer Capacitance	$C_{rss}$		-	0.9	-	
<b>Switching Characteristics<sup>7)</sup></b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 400V, V_{GS} = 10V,$ $I_D = 1A, R_G = 10\Omega$	-	26.4	-	ns
Turn-on Rise Time	$t_r$		-	11.4	-	
Turn-Off Delay Time	$t_{d(off)}$		-	132.1	-	
Turn-Off Fall Time	$t_f$		-	38.1	-	
Total Gate Charge	$Q_g$	$V_{DS} = 480V, V_{GS} = 10V,$ $I_D = 1A$	-	6.1	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.4	-	
Gate-Drain Charge	$Q_{gd}$		-	2.5	-	
Gate Resistance	$R_g$	$f=1MHz$ , Open Drain	-	106.8	-	$\Omega$
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 1A$	-	0.8	1.3	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 1A, V_R = 200V,$ $dI_F/dt = 100A/\mu s$	-	100.6	-	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	419.7	-	$\mu C$
Peak Reverse Recovery Current	$I_{rrm}$		-	8.4	-	A

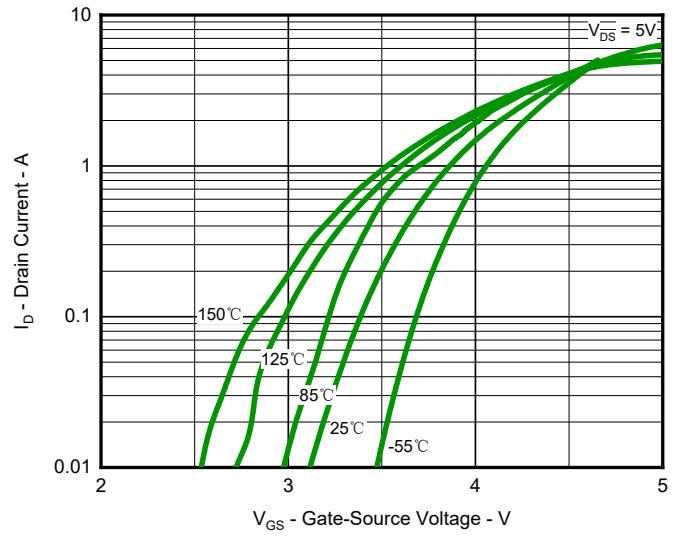
## Notes:

1. Computed continuous current assumes the condition of  $T_{J\_Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature( $T_{J\_Max}=150^\circ C$ ).
3. Pulse Test: Pulse Width  $\leq 10\mu s$ , Duty Cycle  $\leq 1\%$ .
4. This single-pulse measurement was taken under the following condition [ $L=20mH, V_{GS}=10V, V_{DS}=100V$ ]while it's value is limited by  $T_{J\_Max}=150^\circ C$ .
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on infinite heatsink.
7. Guaranteed by design, not subject to production.

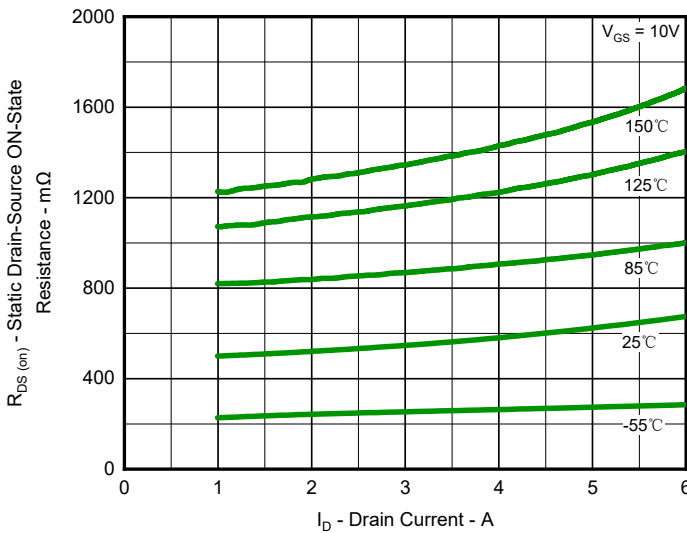
## Typical Characteristics



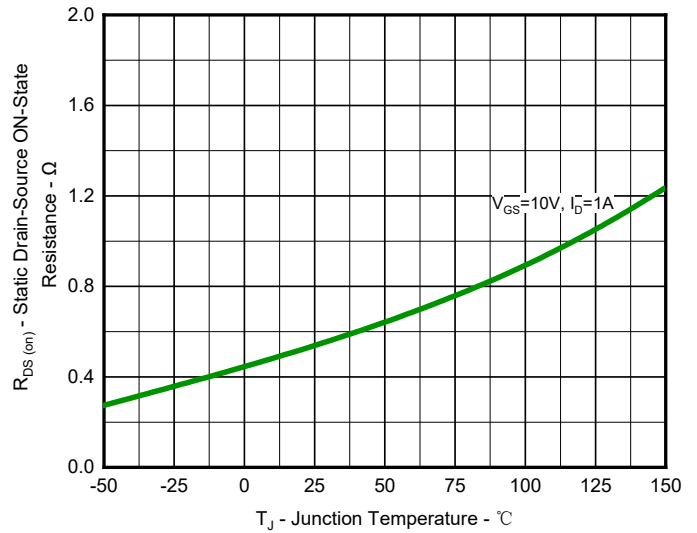
**Fig.1 Output Characteristics**



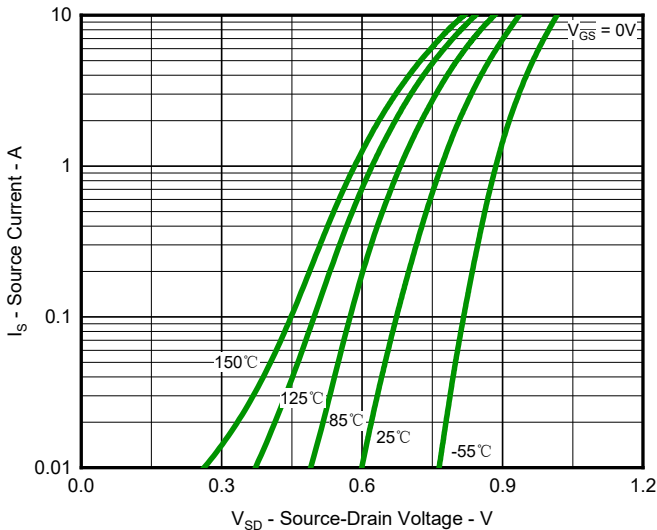
**Fig.2 Typical Transfer Characteristic**



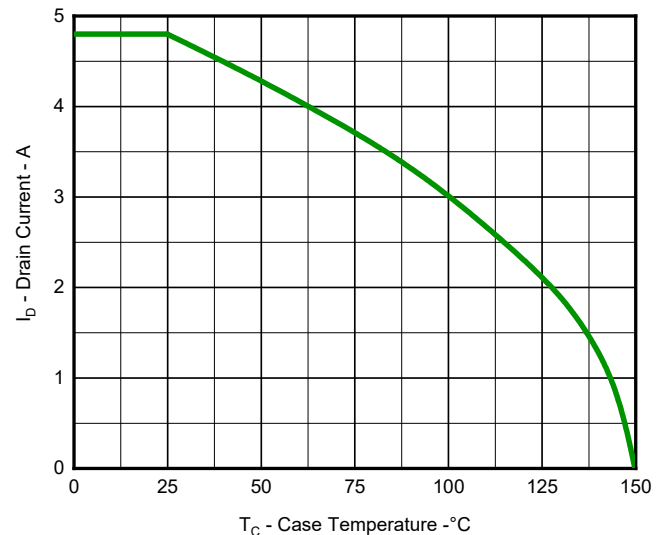
**Fig.3 Typical On-Resistance vs Drain Current and Temperature**



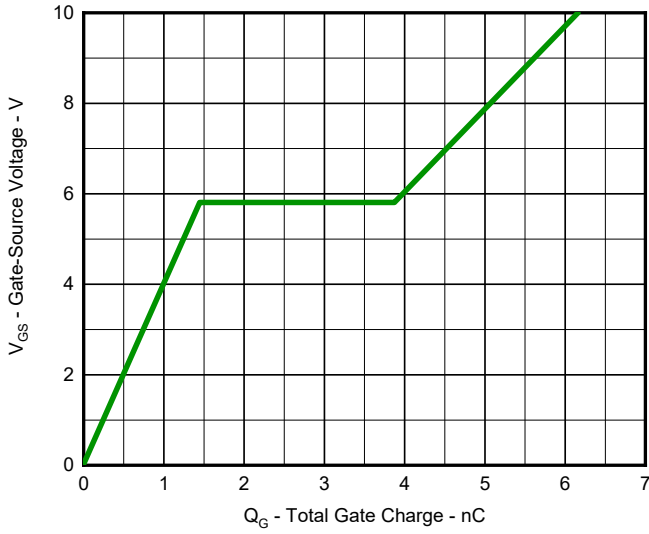
**Fig.4 On-Resistance Variation with Temperature**



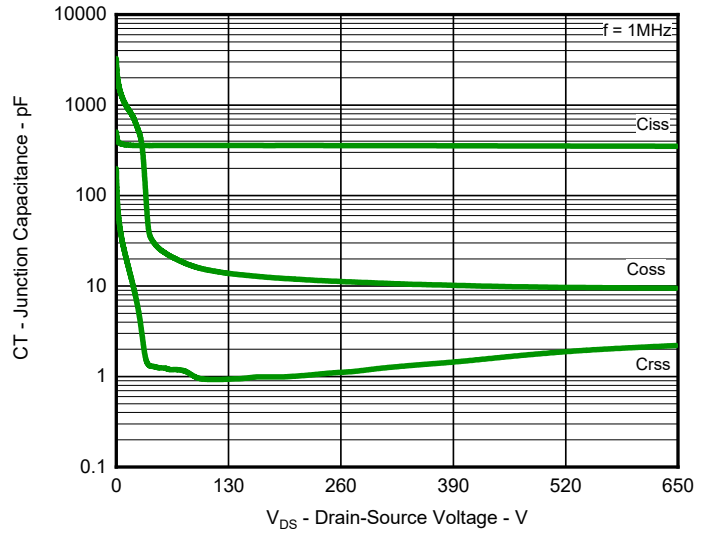
**Fig.5 Diode Forward Voltage vs. Current**



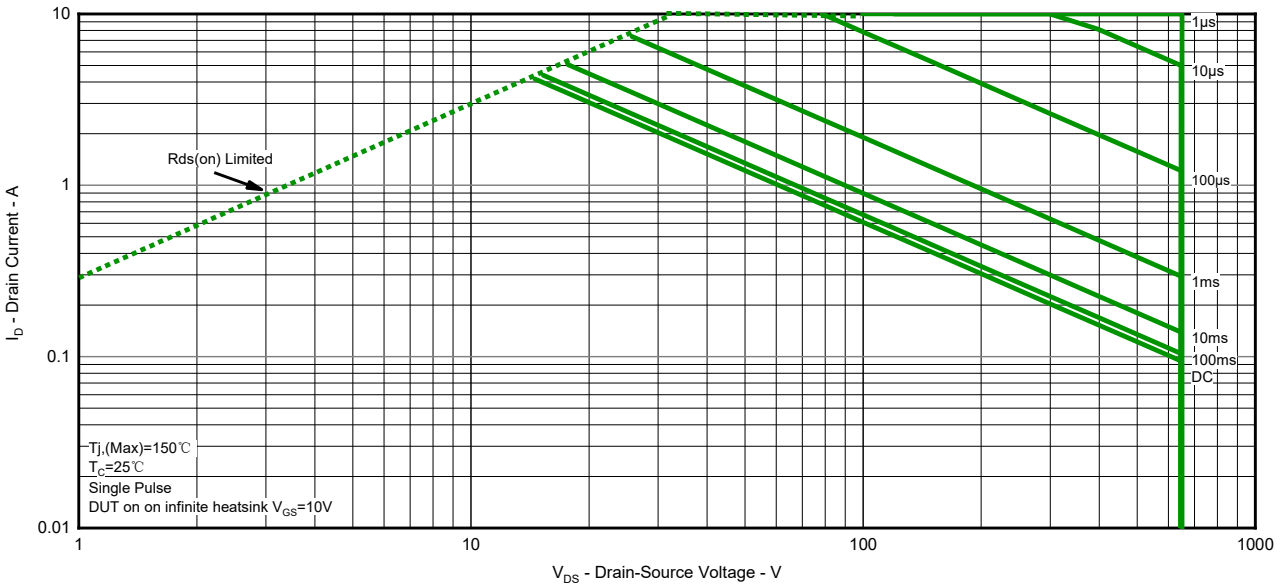
**Fig.6 Maximum Drain Current vs. Case Temperature**



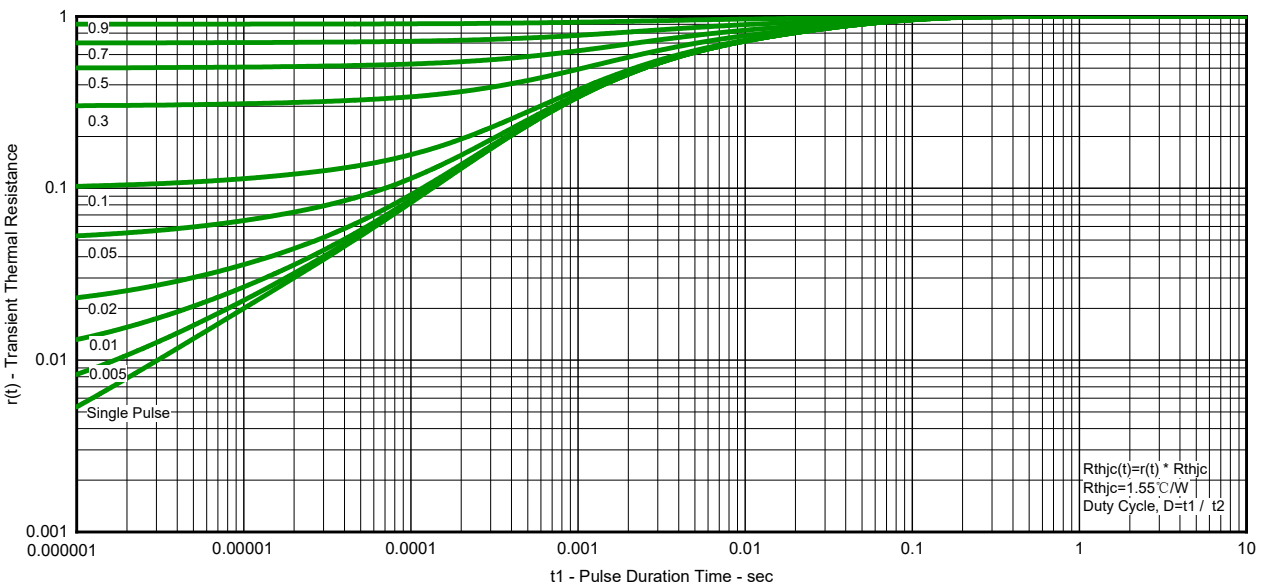
**Fig.7 Gate Charge Characteristics**



**Fig.8 Typical Junction Capacitance**

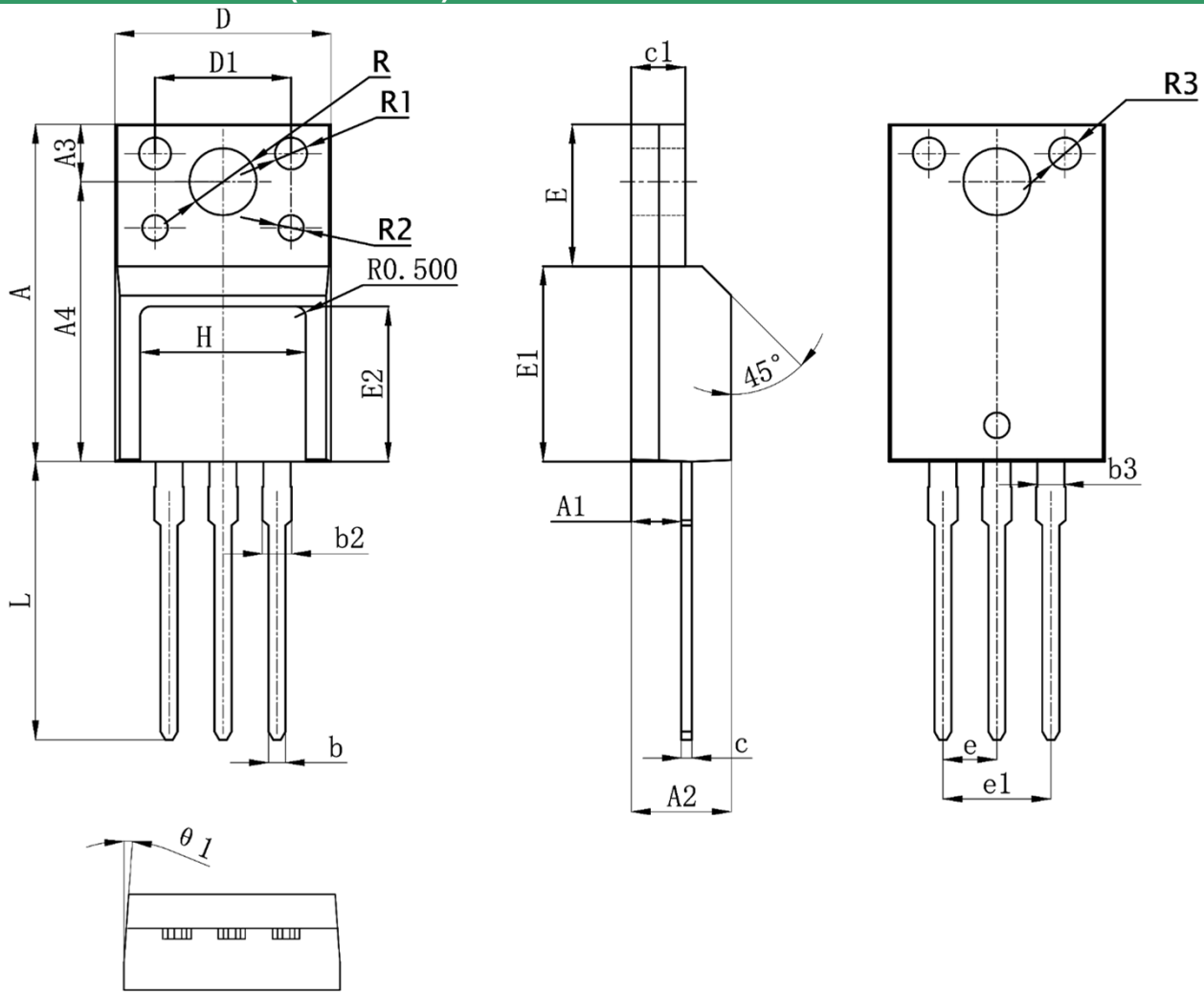


**Fig.9 Safe Operation Area**




**Fig.10 Transient Thermal Resistance**

## Product Dimension (TO-220F)



Dim	Millimeters		Inches		Dim	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	15.67	16.07	0.617	0.633	E	6.48	6.88	0.255	0.271
A1	2.15	2.55	0.085	0.100	E1	8.99	9.39	0.354	0.370
A2	4.50	4.90	0.177	0.193	E2	7.10	7.50	0.280	0.295
A3	3.10	3.50	0.122	0.138	e	2.54 BSC		0.100 BSC	
A4	12.27	12.87	0.483	0.507	e1	5.08 BSC		0.200 BSC	
b	0.77	0.83	0.030	0.033	L	13.14	13.54	0.517	0.533
b2	1.20	1.40	0.047	0.055	R	3.10	3.50	0.122	0.138
b3	1.20 BSC		0.047 BSC		R1	1.50 Ref.		0.059 Ref.	
c	0.40	0.60	0.016	0.024	R2	1.20 Ref.		0.047 Ref.	
c1	2.44	2.64	0.096	0.104	R3	1.50 Ref.		0.059 Ref.	
D	9.86	10.46	0.388	0.412	H	7.60	8.00	0.299	0.315
D1	6.90	7.10	0.272	0.280	$\theta 1$	4°	5°	4°	5°


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